	Parameter		Value40g /TT0 1 Tf -24.986 11.4695	
$_{DS}$				V
V_{GS}				V
I_D	Continuous Drain Current	T_C = 25°C	150	A
		T_C = 100°C	95	
I_{DM}	Pulsed Drain Current (1)		600	A
E_{AS}	Single Pulsed Avalanche Energy (2)		210	mJ
P_D	Power Dissipation	T_C = 25°C	89	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)		56	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.40	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Test Circuit

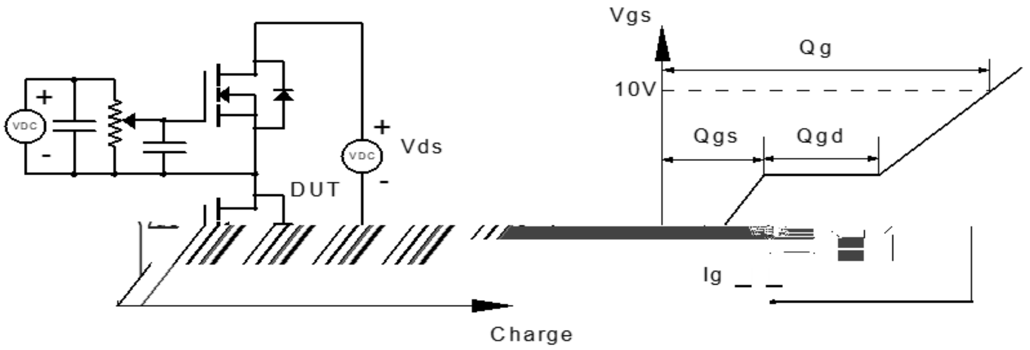

Figure 1: Gate Charge Test Circuit & Waveform

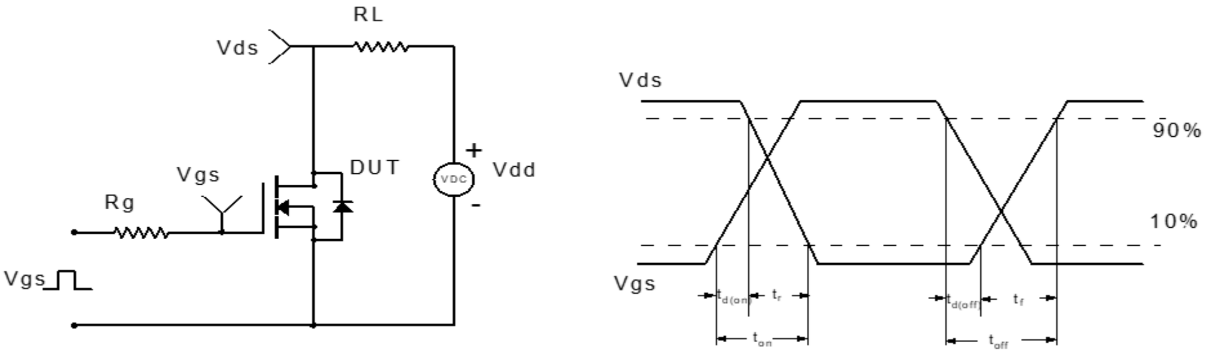

Figure 2: Resistive Switching Test Circuit & Waveform

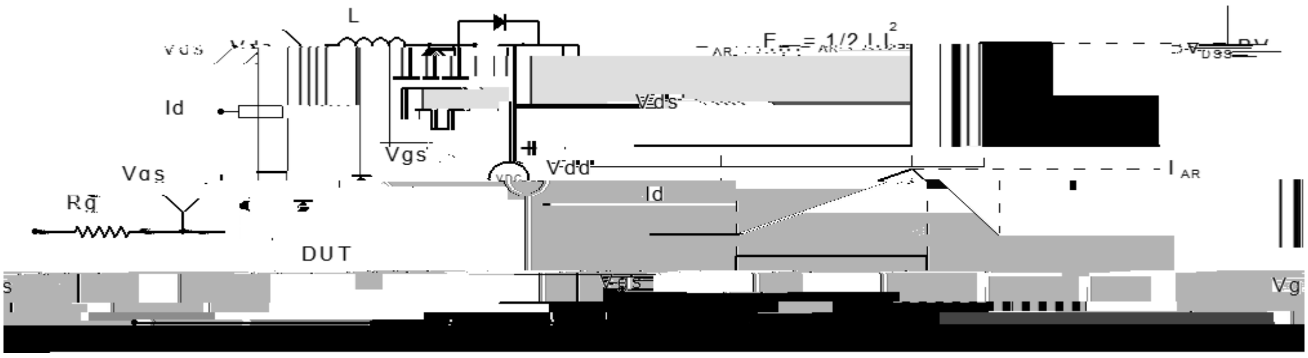

Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

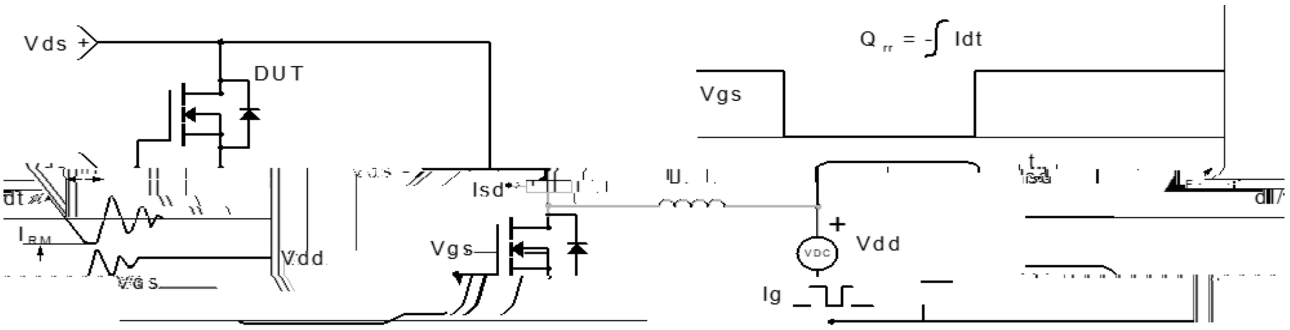

Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-220C-3L)

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